

ABSTRACT OF THE DISCLOSURE

5 A method of manufacturing a semiconductor device includes the steps of forming a copper layer by plating, forming a defect trapping film on the copper layer, moving a defect in the copper layer into the defect trapping film by annealing or the like, and removing the defect trapping film. Thereby, a semiconductor device in which concentration of micro-voids in a portion in proximity to a bottom of a via due to stress migration can be restrained and a method of manufacturing the same can be obtained.